Shih-Yen Lin

List of Publications by Year
in descending order

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147 papers	1,832 citations	331538 21 h-index	315616 38 g-index
147 all docs	147 docs citations	147 times ranked	2210 citing authors

#	Article	IF	Citations
1	Direct Formation of Wafer Scale Graphene Thin Layers on Insulating Substrates by Chemical Vapor Deposition. Nano Letters, 2011, 11, 3612-3616.	4.5	302
2	Near-room-temperature operation of an InAs/GaAs quantum-dot infrared photodetector. Applied Physics Letters, 2001, 78, 2428-2430.	1.5	142
3	High-performance InAs/GaAs quantum-dot infrared photodetectors with a single-sided Al0.3Ga0.7As blocking layer. Applied Physics Letters, 2001, 78, 2784-2786.	1.5	61
4	High-temperature operation normal incident 256/spl times/256 InAs-GaAs quantum-dot infrared photodetector focal plane array. IEEE Photonics Technology Letters, 2006, 18, 986-988.	1.3	61
5	Room-temperature operation type-II GaSb/GaAs quantum-dot infrared light-emitting diode. Applied Physics Letters, 2010, 96, .	1.5	55
6	Establishment of 2D Crystal Heterostructures by Sulfurization of Sequential Transition Metal Depositions: Preparation, Characterization, and Selective Growth. Nano Letters, 2016, 16, 7093-7097.	4.5	51
7	The Growth Mechanism of Transition Metal Dichalcogenides by using Sulfurization of Pre-deposited Transition Metals and the 2D Crystal Hetero-structure Establishment. Scientific Reports, 2017, 7, 42146.	1.6	46
8	Single-Crystal Antimonene Films Prepared by Molecular Beam Epitaxy: Selective Growth and Contact Resistance Reduction of the 2D Material Heterostructure. ACS Applied Materials & Interfaces, 2018, 10, 15058-15064.	4.0	43
9	Toward epitaxially grown two-dimensional crystal hetero-structures: Single and double MoS2/graphene hetero-structures by chemical vapor depositions. Applied Physics Letters, 2014, 105, .	1.5	41
10	800â€‰meV localization energy in GaSb/GaAs/Al0.3Ga0.7As quantum dots. Applied Physics Letters, 2013, 102, .	1.5	38
11	InAs/GaAs quantum dot infrared photodetector (QDIP) with double Al/sub 0.3/Ga/sub 0.7/As blocking barriers. IEEE Transactions on Electron Devices, 2002, 49, 1341-1347.	1.6	33
12	Comparison of InAs/GaAs Quantum Dot Infrared Photodetector and GaAs/(AlGa)As Superlattice Infrared Photodetector. Japanese Journal of Applied Physics, 2001, 40, L1290-L1292.	0.8	31
13	The growth mechanisms of graphene directly on sapphire substrates by using the chemical vapor deposition. Journal of Applied Physics, 2014, 115, .	1.1	29
14	Low-temperature grown graphene films by using molecular beam epitaxy. Applied Physics Letters, 2012, 101, .	1.5	28
15	Influence of doping density on the normal incident absorption of quantum-dot infrared photodetectors. Applied Physics Letters, 2006, 88, 173511.	1.5	27
16	MBE-grown high gate dielectrics of HfO2 and (Hfâ€“Al)O2 for Si and IIIâ€“V semiconductors nano-electronics. Journal of Crystal Growth, 2005, 278, 619-623.	0.7	26
17	Thin single-crystal Sc2O3 films epitaxially grown on Si (111)â€”structure and electrical properties. Journal of Crystal Growth, 2005, 278, 638-642.	0.7	24
18	Singlemode (SMSR>40â€…dB) proton-implanted photonic crystal vertical-cavity surface-emitting lasers. Electronics Letters, 2005, 41, 326.	0.5	24

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19	Ultrafast Exciton Dynamics in Scalable Monolayer MoS₂ Synthesized by Metal Sulfurization. ACS Omega, 2020, 5, 10725-10730.	1.6	23
20	Vertical organic triodes with a high current gain operated in saturation region. Applied Physics Letters, 2006, 89, 183511.	1.5	22
21	Compact microdisk cavity laser with type-II GaSb/GaAs quantum dots. Applied Physics Letters, 2011, 98, 051105.	1.5	21
22	Type-II GaSb/GaAs coupled quantum rings: Room-temperature luminescence enhancement and recombination lifetime elongation for device applications. Applied Physics Letters, 2012, 101, .	1.5	21
23	InN-based heterojunction photodetector with extended infrared response. Optics Express, 2015, 23, 31150.	1.7	21
24	Transport characteristics of InAs/GaAs quantum-dot infrared photodetectors. Applied Physics Letters, 2003, 83, 752-754.	1.5	20
25	InGaAs quantum wire infrared photodetector. Applied Physics Letters, 2007, 91, .	1.5	20
26	Influence of as on the Morphologies and Optical Characteristics of GaSb/GaAs Quantum Dots. IEEE Journal of Quantum Electronics, 2011, 47, 335-339.	1.0	19
27	Room-Temperature Electro-Luminescence of Type-II GaSb/GaAs Quantum Rings. IEEE Photonics Technology Letters, 2012, 24, 1203-1205.	1.3	19
28	Multi-layer elemental 2D materials: antimonene, germanene and stanene grown directly on molybdenum disulfides. Semiconductor Science and Technology, 2019, 34, 105020.	1.0	19
29	Influence of thin metal base thickness on the performance of CuPc vertical organic triodes. Applied Physics Letters, 2007, 90, 153509.	1.5	18
30	Type II GaSb quantum ring solar cells under concentrated sunlight. Optics Express, 2014, 22, A359.	1.7	17
31	Multilayer MoS2 prepared by one-time and repeated chemical vapor depositions: anomalous Raman shifts and transistors with high ON/OFF ratio. Journal Physics D: Applied Physics, 2015, 48, 435101.	1.3	17
32	Voltage-tunable two-color quantum-dot infrared photodetectors. Applied Physics Letters, 2009, 95, 123504.	1.5	16
33	Structural and optical properties of siliconâ€“germanium alloy nanoparticles. Journal of Applied Physics, 2002, 91, 2322-2325.	1.1	15
34	High-Temperature Operation GaSb/GaAs Quantum-Dot Infrared Photodetectors. IEEE Photonics Technology Letters, 2011, 23, 106-108.	1.3	15
35	Pentacene-Based Planar- and Vertical-Type Organic Thin-Film Transistor. IEEE Transactions on Electron Devices, 2007, 54, 1633-1636.	1.6	14
36	Large-Area and Strain-Reduced Two-Dimensional Molybdenum Disulfide Monolayer Emitters on a Three-Dimensional Substrate. ACS Applied Materials & Interfaces, 2019, 11, 26243-26249.	4.0	14

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37	All-organic hot-carrier triodes with thin-film metal base. Applied Physics Letters, 2006, 89, 183508.	1.5	13
38	Passivated graphene transistors fabricated on a millimeter-sized single-crystal graphene film prepared with chemical vapor deposition. Journal Physics D: Applied Physics, 2015, 48, 295106.	1.3	13
39	Layer number controllability of transition-metal dichalcogenides and the establishment of hetero-structures by using sulfurization of thin transition metal films. Journal Physics D: Applied Physics, 2017, 50, 064001.	1.3	13
40	Atomic layer etchings of transition metal dichalcogenides with post healing procedures: equivalent selective etching of 2D crystal hetero-structures. 2D Materials, 2017, 4, 034001.	2.0	13
41	Large Surface Photovoltage of WS₂/MoS₂ and MoS₂/WS₂ Vertical Hetero-bilayers. ACS Applied Electronic Materials, 2021, 3, 2601-2606.	2.0	13
42	InGaAs-Capped InAsâ€“GaAs Quantum-Dot Infrared Photodetectors Operating in the Long-Wavelength Infrared Range. IEEE Photonics Technology Letters, 2009, 21, 1332-1334.	1.3	12
43	Spherical SiGe quantum dots prepared by thermal evaporation. Applied Physics Letters, 2000, 77, 4328-4329.	1.5	11
44	Effect of Silicon Dopant on the Performance of InAs/GaAs Quantum-Dot Infrared Photodetectors. Japanese Journal of Applied Physics, 2004, 43, L167-L169.	0.8	11
45	The transition mechanisms of type-II GaSb/GaAs quantum-dot infrared light-emitting diodes. Journal of Crystal Growth, 2011, 323, 466-469.	0.7	11
46	Scalable MoS₂/graphene hetero-structures grown epitaxially on sapphire substrates for phototransistor applications. Semiconductor Science and Technology, 2018, 33, 025007.	1.0	11
47	Quantum-dot infrared photodetectors with p-type-doped GaAs barrier Layers. IEEE Photonics Technology Letters, 2005, 17, 2409-2411.	1.3	10
48	Structural and optical properties of germanium nanoparticles. Journal of Applied Physics, 2002, 91, 1525-1528.	1.1	9
49	Transport mechanisms and the effects of organic layer thickness on the performance of organic Schottky diodes. Journal of Vacuum Science & Technology B, 2007, 25, 43.	1.3	9
50	Enhanced Normal-Incident Absorption of Quantum-Dot Infrared Photodetectors With Smaller Quantum Dots. IEEE Photonics Technology Letters, 2008, 20, 1240-1242.	1.3	9
51	Memory device application of wide-channel in-plane gate transistors with type-II GaAsSb-capped InAs quantum dots. Applied Physics Letters, 2013, 103, 143502.	1.5	9
52	Lasing action and extraordinary reduction in long radiative lifetime of type-II GaSb/GaAs quantum dots using circular photonic crystal nanocavity. Applied Physics Letters, 2015, 107, .	1.5	9
53	The atomic layer etching of molybdenum disulfides using low-power oxygen plasma. Semiconductor Science and Technology, 2019, 34, 045007.	1.0	9
54	Temperature dependence of carrier dynamics for InAsâˆ•GaAs quantum dot infrared photodetectors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1909.	1.6	8

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55	In-Plane Gate Transistors Fabricated by Using Atomic Force Microscopy Anode Oxidation. IEEE Electron Device Letters, 2010, , .	2.2	8
56	In-Plane Gate Transistors With a 40-$muhbox{m}$-Wide Channel Width. IEEE Electron Device Letters, 2012, 33, 1129-1131.	2.2	8
57	The formation mechanisms and optical characteristics of GaSb quantum rings. Journal of Applied Physics, 2013, 114, .	1.1	8
58	Defect formation and modulation during patterning supported graphene sheets using focused ion beams. Materials Today Communications, 2018, 17, 60-68.	0.9	8
59	Highly conductive nanometer-thick gold films grown on molybdenum disulfide surfaces for interconnect applications. Scientific Reports, 2020, 10, 14463.	1.6	8
60	Van der Waals Epitaxy of Large-Area and Single-Crystalline Gold Films on MoS₂ for Low-Contact-Resistance 2Dâ€“3D Interfaces. ACS Applied Nano Materials, 2020, 3, 2997-3003.	2.4	8
61	The influence of In composition on InGaAs-capped InAs/GaAs quantum-dot infrared photodetectors. Journal of Applied Physics, 2009, 106, .	1.1	7
62	Investigations for InAs/GaAs multilayered quantum-dot structure treated by high energy proton irradiation. Thin Solid Films, 2010, 518, 7425-7428.	0.8	7
63	Performance Improvement of AlGaAs/GaAs QWIP by ${m NH}_{3}$ Plasma Treatment. IEEE Journal of Quantum Electronics, 2012, 48, 922-926.	1.0	7
64	The influence of background As on GaSb/GaAs quantum dots and its application in infrared photodetectors. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 314-317.	0.8	7
65	Formation and Characterization of 1.5-Monolayer Self-Assembled InAs/GaAs Quantum Dots Using Postgrowth Annealing. IEEE Nanotechnology Magazine, 2007, 6, 589-594.	1.1	6
66	Enhancement of field-effect mobility in molybdenum-disulfide transistor through the treatment of low-power oxygen plasma. Japanese Journal of Applied Physics, 2016, 55, 090302.	0.8	6
67	Layered Graphene Growth Directly on Sapphire Substrates for Applications. ACS Omega, 2022, 7, 13128-13133.	1.6	6
68	Title is missing!. Journal of Nanoparticle Research, 2001, 3, 489-492.	0.8	5
69	High responsivity quantum-dot infrared photodetector with blocking layers at both sides of the structure. Journal of Crystal Growth, 2005, 278, 351-354.	0.7	5
70	Device simulation for GaAsâˆ•AlGaAs superlattice infrared photodetector with a single current blocking layer. Journal of Applied Physics, 2005, 97, 064910.	1.1	5
71	Temperature-insensitive detectivity of 5-pair InAs/GaAs quantum-dot infrared photodetectors with asymmetric device structure. Journal of Crystal Growth, 2007, 301-302, 817-820.	0.7	5
72	In-Plane Gate Transistors for Photodetector Applications. IEEE Electron Device Letters, 2013, 34, 780-782.	2.2	5

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73	Luminescence Enhancement and Enlarged Dirac Point Shift of MoS2/Graphene Hetero-Structure Photodetectors With Postgrowth Annealing Treatment. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 101-105.	1.9	5
74	Charge Storage of Isolated Monolayer Molybdenum Disulfide in Epitaxially Grown MoS₂/Graphene Heterostructures for Memory Device Applications. ACS Applied Materials & Interfaces, 2021, 13, 45864-45869.	4.0	5
75	Nanometer-thick copper films with low resistivity grown on 2D material surfaces. Scientific Reports, 2022, 12, 1823.	1.6	5
76	Influences of silicon doping in quantum dot layers on optical characteristics of InAs/GaAs quantum dot infrared photodetector. Thin Solid Films, 2007, 515, 4459-4461.	0.8	4
77	Site-controlled self-assembled InAs quantum dots grown on GaAs substrates. Nanotechnology, 2010, 21, 295304.	1.3	4
78	Improved 1.3-$mu{m m}$ Electroluminescence of InGaAs-Capped Type-II GaSb/GaAs Quantum Rings at Room Temperature. IEEE Photonics Technology Letters, 2013, 25, 97-99.	1.3	4
79	Fermi-level shifts in graphene transistors with dual-cut channels scraped by atomic force microscope tips. Applied Physics Letters, 2014, 104, 023511.	1.5	4
80	Type-II Superlattice Infrared Photodetectors With Graphene Transparent Electrodes. IEEE Photonics Technology Letters, 2017, 29, 1691-1694.	1.3	4
81	Tungsten Diselenide Top-gate Transistors with Multilayer Antimonene Electrodes: Gate Stacks and Epitaxially Grown 2D Material Heterostructures. Scientific Reports, 2020, 10, 5967.	1.6	4
82	MoS2 with Stable Photoluminescence Enhancement under Stretching via Plasmonic Surface Lattice Resonance. Nanomaterials, 2021, 11, 1698.	1.9	4
83	Luminescence enhancement and dual-color emission of stacked mono-layer 2D materials. Nanotechnology, 2020, 31, 365702.	1.3	4
84	High-performance 30-period quantum-dot infrared photodetector. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2005, 23, 1129.	1.6	3
85	The influence of InAs coverage on the performances self-assembled InGaAs quantum rings. Journal of Crystal Growth, 2007, 301-302, 841-845.	0.7	3
86	Quantum-dot/quantum-well mixed-mode infrared photodetectors for multicolor detection. Applied Physics Letters, 2008, 92, 253510.	1.5	3
87	The transition mechanisms of a ten-period InAsâˆ•GaAs quantum-dot infrared photodetector. Journal of Vacuum Science & Technology B, 2008, 26, 1831-1833.	1.3	3
88	The influence of interface roughness on the normal incident absorption of quantum-well infrared photodetectors. Thin Solid Films, 2009, 517, 1799-1802.	0.8	3
89	The fabrication of nanomesas and nanometal contacts by using atomic force microscopy lithography. Journal of Applied Physics, 2010, 108, 094316.	1.1	3
90	Transition mechanism of InAs/GaAs quantum-dot infrared photodetectors with different InAs coverages. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C3G28-C3G31.	0.6	3

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91	Two-Color Qauntum-Dot Infrared Photodetectors With Periodic Cross Metal Hole Array Contact. IEEE Photonics Technology Letters, 2010, 22, 577-579.	1.3	3
92	Graphitic carbon film formation under Ni templates by radio-frequency sputtering for transparent electrode applications. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, .	0.6	3
93	Broadband InGaAs-capped InAs/GaAs quantum-dot infrared photodetector with Bi-modal dot height distributions. Journal of Applied Physics, 2012, 112, 034508.	1.1	3
94	The operation principle of the well in quantum dot stack infrared photodetector. Journal of Applied Physics, 2013, 114, 244504.	1.1	3
95	Enhanced responsivity and detectivity values of short 30-period InAs/GaSb type-II infrared photodetectors with reduced device areas. Japanese Journal of Applied Physics, 2016, 55, 04EH07.	0.8	3
96	Photonic Crystal Circular Nanobeam Cavity Laser with Type-II GaSb/GaAs Quantum Rings as Gain Material. Scientific Reports, 2020, 10, 4757.	1.6	3
97	Optical Mode Tuning of Monolayer Tungsten Diselenide (WSe2) by Integrating with One-Dimensional Photonic Crystal through Excitonâ€“Photon Coupling. Nanomaterials, 2022, 12, 425.	1.9	3
98	High temperature operated (â^¼250 K) photovoltaic-photoconductive (PV-PC) mixed-mode InAs/GaAs quantum dot infrared photodetector. , 0, , .		2
99	Integral and fractional charge filling in a InAs/GaAs quantum dot pâ€“iâ€“n diode by capacitanceâ€“voltage measurement. Journal of Applied Physics, 2002, 91, 6700.	1.1	2
100	Surface morphology and photoluminescence of InAs quantum dots grown on [11~0]-oriented streaked islands under ultra-low V/III ratio. IEEE Nanotechnology Magazine, 2004, 3, 275-280.	1.1	2
101	Self-ordered InGaAs quantum dots grown at low growth rates. Journal of Applied Physics, 2008, 103, 044301.	1.1	2
102	Tailoring detection wavelength of InGaAs quantum wire infrared photodetector. Journal of Vacuum Science & Technology B, 2008, 26, 1140.	1.3	2
103	Temperature-dependent photoluminescence and carrier dynamics of standard and coupled type-II GaSb/GaAs quantum rings. Journal of Crystal Growth, 2013, 378, 426-429.	0.7	2
104	Graphene films grown at low substrate temperature and the growth model by using MBE technique. Journal of Crystal Growth, 2013, 378, 333-336.	0.7	2
105	Electronic Properties and Density of States of Self-Assembled GaSb/GaAs Quantum Dots. Journal of Nanotechnology, 2013, 2013, 1-5.	1.5	2
106	Positioning effect of type-II GaSb/GaAs quantum ring layer on solar cell performances. , 2015, , .		2
107	GaSb/GaAs quantum dots and rings grown under periodical growth mode by using molecular beam epitaxy. Journal of Crystal Growth, 2015, 425, 283-286.	0.7	2
108	Current Enhancement and Bipolar Current Modulation of Top-Gate Transistors Based on Monolayer MoS2 on Three-Layer WxMo1â€“xS2. ACS Applied Materials & Interfaces, 2018, 10, 24733-24738.	4.0	2

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109	Transfer current in p-type graphene/MoS2 heterostructures. Physica E: Low-Dimensional Systems and Nanostructures, 2021, 125, 114383.	1.3	2
110	Top-gate transistors fabricated on epitaxially grown molybdenum disulfide and graphene hetero-structures. Applied Physics Express, 2021, 14, 125502.	1.1	2
111	Observation of self-assembled InAs/GaAs quantum dot structure with temperature-dependent photoluminescence and measurement of electrical characteristics. , 2000, 4078, 115.		1
112	<title>Investigation of supperlattice infrared photodetectors to reach the background-limited performance at high temperature</title>. , 2001, 4288, 151.		1
113	The transition mechanisms of quantum-dot/quantum-well mixed-mode infrared photodetectors. Infrared Physics and Technology, 2009, 52, 268-271.	1.3	1
114	Enhancement of operation temperature of InAsâˆ•GaAs quantum-dot infrared photodetectors with hydrogen-plasma treatment. Journal of Vacuum Science & Technology B, 2009, 27, 2102.	1.3	1
115	Broadband Quantum-Dot Infrared Photodetector. IEEE Photonics Technology Letters, 2010, 22, 963-965.	1.3	1
116	Room-temperature operation type-II GaSb/GaAs quantum-dot infrared light-emitting diode. , 2010, , .		1
117	Wavelength-tunable InGaAs-capped quantum-dot infrared photodetectors for multi-color detection. Infrared Physics and Technology, 2011, 54, 220-223.	1.3	1
118	Long-wavelength electroluminescence of InGaAs-capped type-II GaSb/GaAs quantum-rings at room temperature. Journal of Crystal Growth, 2013, 378, 571-575.	0.7	1
119	Transferring-free and large-area graphitic carbon film growth by using molecular beam epitaxy at low growth temperature. Journal of Crystal Growth, 2015, 425, 177-180.	0.7	1
120	11-Î¼m InAs/GaAs quantum-dot light-emitting transistors grown by molecular beam epitaxy. Optics Letters, 2015, 40, 3747.	1.7	1
121	Long-Wavelength In-Plane Gate InAs Quantum-Dot Phototransistors. IEEE Photonics Technology Letters, 2015, 27, 261-263.	1.3	1
122	Internal Fields in Multilayer WS 2 /MoS 2 Heterostructures Epitaxially Grown on Sapphire Substrates. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 2000033.	0.8	1
123	Temperature-stable (wavelength â^¼ 1 Î¼m) InAs/GaAs quantum dot light-emitting diode. , 0, , .		0
124	Surface morphology and photoluminescence of InAs quantum dots grown on [110]-oriented streaked-islands under ultralow V/III ratio. , 2003, , .		0
125	Single mode (SMSR > 40 dB) proton-implanted photonic crystal vertical-cavity surface-emitting lasers. , 2005, , .		0
126	Single-Period InAsâ€“GaAs Quantum-Dot Infrared Photodetectors. IEEE Photonics Technology Letters, 2008, 20, 1575-1577.	1.3	0

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127	Influence of As-stabilized surface on the formation of InAsâˆ•GaAs quantum dots. Journal of Vacuum Science & Technology B, 2008, 26, 956.	1.3	0
128	High-Responsivity InGaAs/InP Quantum-Well Infrared Photodetectors Prepared by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2009, 48, 04C108.	0.8	0
129	Wavelength-Tunable InGaAs-Capped Quantum-Dot Infrared Photodetectors. IEEE Photonics Technology Letters, 2010, 22, 227-229.	1.3	0
130	GaSb/GaAs quantum dots with type-II band alignments prepared by molecular beam epitaxy for device applications. , 2011, , .		0
131	Painted graphitic carbon films formed underneath Ni templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 179-182.	0.8	0
132	6.5 nm-thick Al<inf>2</inf>O<inf>3</inf> Surface passivated layer grown on two stacks of 10-period InGaAs and GaAs-capped InAs Quantum Dot Infrared Photodetector Focal Plane Arrays for high temperature operation. , 2013, , .		0
133	Field effect of in-plane gates with different gap sizes on the Fermi level tuning of graphene channels. Applied Physics Letters, 2014, 104, 183503.	1.5	0
134	High temperature operation In(Ga)As quantum dot infrared photodetector focal plane arrays passivated with 6.5 nm-thick Al<SUB align="right">2O<SUB align="right">3 layer. International Journal of Nanotechnology, 2014, 11, 345.	0.1	0
135	Optical properties of InN-based photodetection devices. , 2015, , .		0
136	InN nanopillar devices with strong photoresponse. , 2016, , .		0
137	Multiple-layered type-II GaSb/GaAs quantum ring solar cells under concentrated solar illumination. , 2016, , .		0
138	Type-I to Type-II Transformation of Hybrid Quantum Nanostructures. IEEE Journal of Selected Topics in Quantum Electronics, 2017, 23, 1-7.	1.9	0
139	Dual-cut graphene transistors with constant-current regions fabricated by the atomic force microscope anode oxidation. Japanese Journal of Applied Physics, 2017, 56, 010307.	0.8	0
140	Preparation of Large-area Vertical 2D Crystal Hetero-structures Through the Sulfurization of Transition Metal Films for Device Fabrication. Journal of Visualized Experiments, 2017, , .	0.2	0
141	Enhanced Absorption Due to Formation of Quasi-Bound States in Type-II Coupled Quantum Rings. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-7.	1.9	0
142	Long Photon Lifetime from Microdisk Cavity Laser with Type II GaSb/GaAs Quantum Dots. , 2013, , .		0
143	A ZnO/InN/GaN Heterojunction Photodetector with Extended Infrared Response. , 2015, , .		0
144	A Single InN Nanopillar Photodetector with Extended Infrared Response Grown by MOCVD. , 2016, , .		0

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145	Absorption enhancement in type-II coupled quantum rings due to existence of quasi-bound states. , 2018, , .		0
146	Stable Photoluminescence Enhancement of MoS2 Buried in PDMS via Plasmonic Surface Lattice Resonance. , 2020, , .		0
147	Strain reduced and photoluminescence enhanced of MoS2 emitters on three-dimensional substrate. , 2020, , .		0